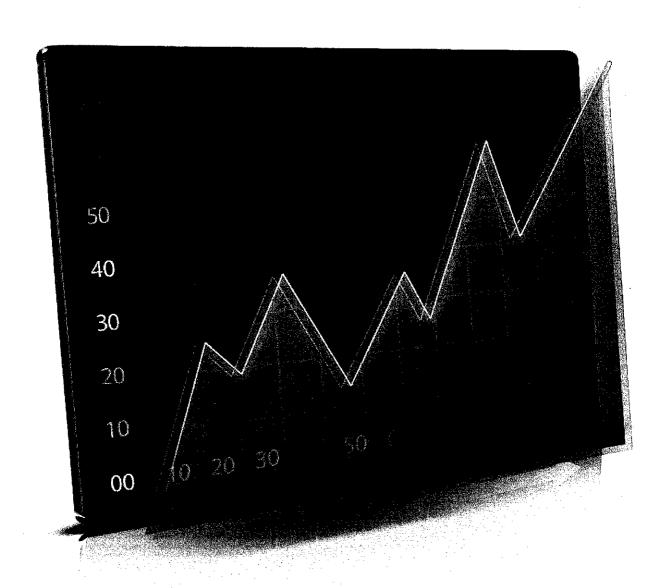


# System Performance Booklet

DZ936N-BEX2-DD\_1





### System Overview

Description Model				Serial Number					
CCD Head	D	Z	9	36N	1	BEX2-DD		CCI	0-19270
TE Cooler performance (	(*)					High			Ultra-high ✓
Power Supply Units						PS -29			PS -40
						<b>y</b>			<b>✓</b>
Accessories					LM-			MFL-	
Serial/Batch Number									
Other									

 $\nabla$  Sensor types are defined in Table 1 using the last two letters in box Model Number.

#### **CCD Details**

Manufacturer / Model No.		Pixels	Serial Number
E2V CCD42-40		2048x2048, 13.5μm x 13.5μm	12321-12-01
	AFFAAAAAAA	The state of the s	

Special Features	(*)		(*)
NIMO		Nikon F-mount with Shutter	<b>~</b>
Fringe Suppression		Custom Cables	
Shielded Anti-Blooming			

Window Variant	(*)		(~)
VUV-UV Parallel		NUV-Enhanced Parallel	
Broadband VUV-NIR Wedged		Broadband VUV-NIR Parallel	~
Broadband VIS-NIR Wedged		Broadband VIS-NIR Parallel	
VIS-NIR Enhanced Wedged		Bose-Einstein 780nm Wedged	
None		Other	

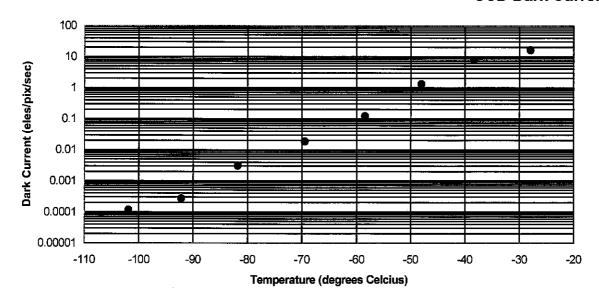


### **Summary of System Test Data**

#### Readout Noise +1 and Base Mean Level +2

		CCD Sen	sitivity +3	Single Pi	xel Noise	Base Me	an Level
A/D Rate	Preamp	e- per A	/D count	electro	ns rms	A/D counts	
MHz - all 16 bit	setting	High Sensitivity Mode	High Capacity Mode	High Sensitivity Mode	High Capacity Mode	High Sensitivity Mode	High Capacity Mode
5.0	<b>x</b> 1	7.0	20.8	41.7	107.8	2340	1149
5.0	x2	3.7	13.2	33.2	91.1	3622	1345
5.0	<b>x4</b>	1.9	6.8	24.0	66.9	4635	1844
3.0	x1	4.9	18.8	29.4	91.8	941	876
3.0	x2	2.5	9.7	15.3	54.5	1580	1434
3.0	x4	1.1	5.3	10.4	43.0	2173	2511
1.0	x1	4.4	18.4	10.3	40.9	891	1162
1.0	<b>x</b> 2	2.3	10.1	7.8	30.7	1343	1848
1.0	х4	1.1	5.0	6.5	26.7	2171	3122
0.05	x1	4.4	19.1	5.9	18.9	917	1178
0.05	<b>x2</b>	2.2	9.6	5.0	13.7	1353	1844
0.05	<b>x4</b>	1.1	5.4	4.3	13.6	2166	3082
Saturatio	n Signal per	pixel <i>◆14</i>		17411	7	electrons	

#### **CCD Dark Current**



Minimum Dark Current Achievable ≠4	0.000117	electro	ons/pixel/s	ec.
@ Sensor Temperature of ◆5	-101.96	°C	16.0	°C cooling water
CCD Dark Current Uniformity better than ▶6	0.870825 electrons/pixel/sec		ec	



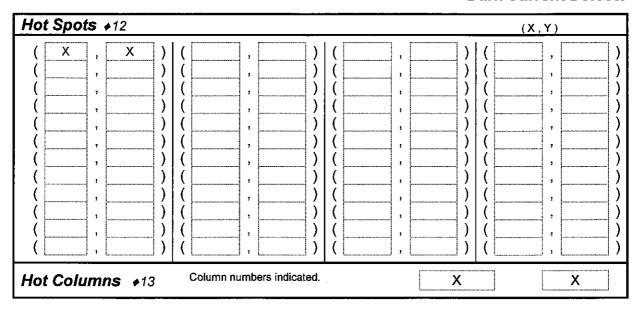
#### **Linearity and Uniformity**

Linearity better than ≠7	1	% over 16 bits
Response Uniformity better than ◆8	1.91	%

#### **Response Defects**

White/Black Spots +9				(X,Y) Number of Pixels
X , Y	Number of Pixels	Χ,	Υ	Number of Pixels
( 1340 , 2020 ) ( X , X ) ( , , ) ( ,	1 X			
White/Black Columns Column numbers indicated.  Traps •11	◆10 Column numbers indicated.		2044 X	

#### **Dark Current Defects**





#### **Test Conditions**

Readout Noise tested at	-90	°C with	16	°C water
Base Mean Level measured at	-90	°C with	16	°C water
Dark Current Uniformity tested at	-50	°C with	16	°C water
Blemishes tested at	-50	°C with	16	°C water

**Custom Testing** 

Signed

**System Passed for Shipping** 

Date

K.MCDOWELL

29<sup>TH</sup> APRIL 2016

## abla Table 1; Key code to define the meanings of the last two letters in the Model Number

	Sensor Options						
OE	Open electrode	BV	BI + VIS (550nm) optimised)				
됴	Front illuminated (FI)	BR	BI + NIR (850) optimised				
5	FI+UV coating	BR-DD	BI + NIR +deepdepletion				
FO	FI + Fibre optic	BN	Bl with no AR coating				
FI-DD	FI + deep depletion	FK	Fast Kinetics (masked; 3011 only)				
BU2	Back Illuminated (BI) + 250nm UV optimised	KT	Kodak FI coating				
BU	BI + UV (350nm) optimised						



#### **Performance Notes**

- 1 Readout Noise is measured for both single pixel (SP) and fully vertically binned (FVB) with the CCD in darkness at temperature indicated and minimum exposure time. Noise values will change with preamplifier gain selection [PAG].
- ◆2 Average electronic DC offset for CCD in darkness at temperature indicated and minimum exposure time under dark conditions measured by single pixel (SP) for imaging systems and by (FVB) for spectroscopic systems.
- ◆3 Sensitivity is calculated in photoelectrons per A/D count from measurements of the Photon Transfer Curves.
- Dark current falls exponentially with temperature. However, for a given temperature the actual dark current can vary by more than an order of magnitude from device to device. The devices are specified in terms of minimum dark current achievable rather than minimum temperature.
- ◆5 Minimum temperature achieved for thermoelectric (TE) cooler set to maximum value with water cooling
- ♠6 RMS (root mean square) deviation of dark current for fully binned operation for spectroscopic cameras, or full resolution image for imaging cameras, under dark conditions at temperature indicated (pixel/column defects not included). This variation is mainly cosmetic since it is fully subtractable without significant loss of performance.
- ♦7 Linearity is measured from a plot of Counts vs. Signal over the 16 bit dynamic range. Linearity is expressed as a %age deviation from a straight line fit. This quantity is not measured on individual systems.
- ♠8 RMS (root mean square) deviation from the average response of the CCD in fully binned operation for spectroscopic cameras, or full resolution image for imaging cameras, illuminated with uniform white light (defects not included).
- ♦9 White/black spots have signals >25% above/below the average (i.e >25% contrast) with uniform illumination across the sensor.
- ◆10 Columns whose signals have >10% contrast in binned operation with uniform illumination across the sensor for spectroscopic cameras, ≥ 10 black spots per column for imaging cameras.
- ◆11 Pixels which absorb charge as it is clocked through the defective area. When the light source is switched off, the signal from the trap appears to drop off more slowly than the signal from the surrounding pixels.
- ♦ 12 A spot can be up to 3 pixels in size. For Grade A devices, hot spots are counted if they exhibit >50 times the maximum specified dark current at the test temperature indicated.
- ◆13 A column is considered defective if >10 pixels are affected, or if the column exhibits >2 times the maximum specified dark current at the test temperature indicated.
- ◆14 Saturation Signal per pixel is measured at 1MHz PreAmp x1 High Sensitivity mode